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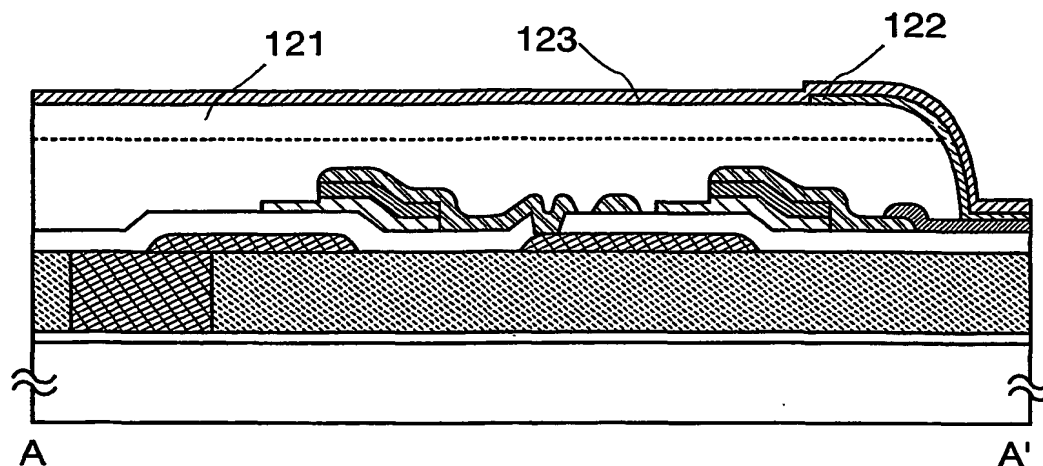
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(54) Title: DISPLAY DEVICE, METHOD FOR MANUFACTURING THE SAME, AND TELEVISION APPARATUS



(57) Abstract: An object of the present invention is to provide a display device which can be manufactured with usability of a material improved and with a manufacturing step simplified and to provide a manufacturing technique thereof. One feature of a display device of the present invention is to comprise an insulating layer having an opening, a first conductive layer formed in the opening, and a second conductive layer formed over the insulating layer and the first conductive layer, wherein the first conductive layer is wider and thicker than the second conductive layer, and the second conductive layer is formed by spraying a droplet including a conductive material.

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